

N0903L Process Geometry

Features

- Low Noise: 0.7 nV/√Hz Typical
- Typical Input Capacitance: 50pF
- Typical Breakdown Voltage: -30V
- High Input Impedance
- Die Size: 975um X 975um X 203um
- Bond Pads: 90um X 90um
- Substrate Connected to Gate
- Au Back-Side Finish

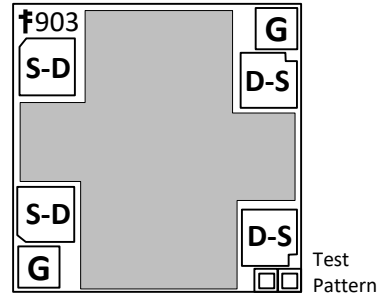
Applications

- Low Noise Amplifier
- Audio Amplifiers
- Matched Pair Applications
- Custom Part Options

Description

The InterFET N0903L Geometry is ideal for low noise high gain applications.

Geometry Top View



Standard Parts

- IF9030
- IFN5432, IFN5433, IFN5434

Product Summary

Parameters	Min	Typ	Max	Unit
BV _{GSS} Gate to Source Breakdown Voltage	-25	-30		V
I _{DSS} Drain to Source Saturation Current	10		500	mA
V _{GS(off)} Gate to Source Cutoff Voltage	-0.3		-3	V
G _{FS} Forward Transconductance		250		mS

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

Parameters	Min	Typ	Max	Unit
V _{RGS} Reverse Gate to Source or Drain Voltage	-20	-30		V
I _{FG} Continuous Forward Gate Current			10	mA
T _J Operating Junction Temperature	-55		150	°C
T _{STG} Storage Temperature	-65		175	°C



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.

Electrical Characteristics

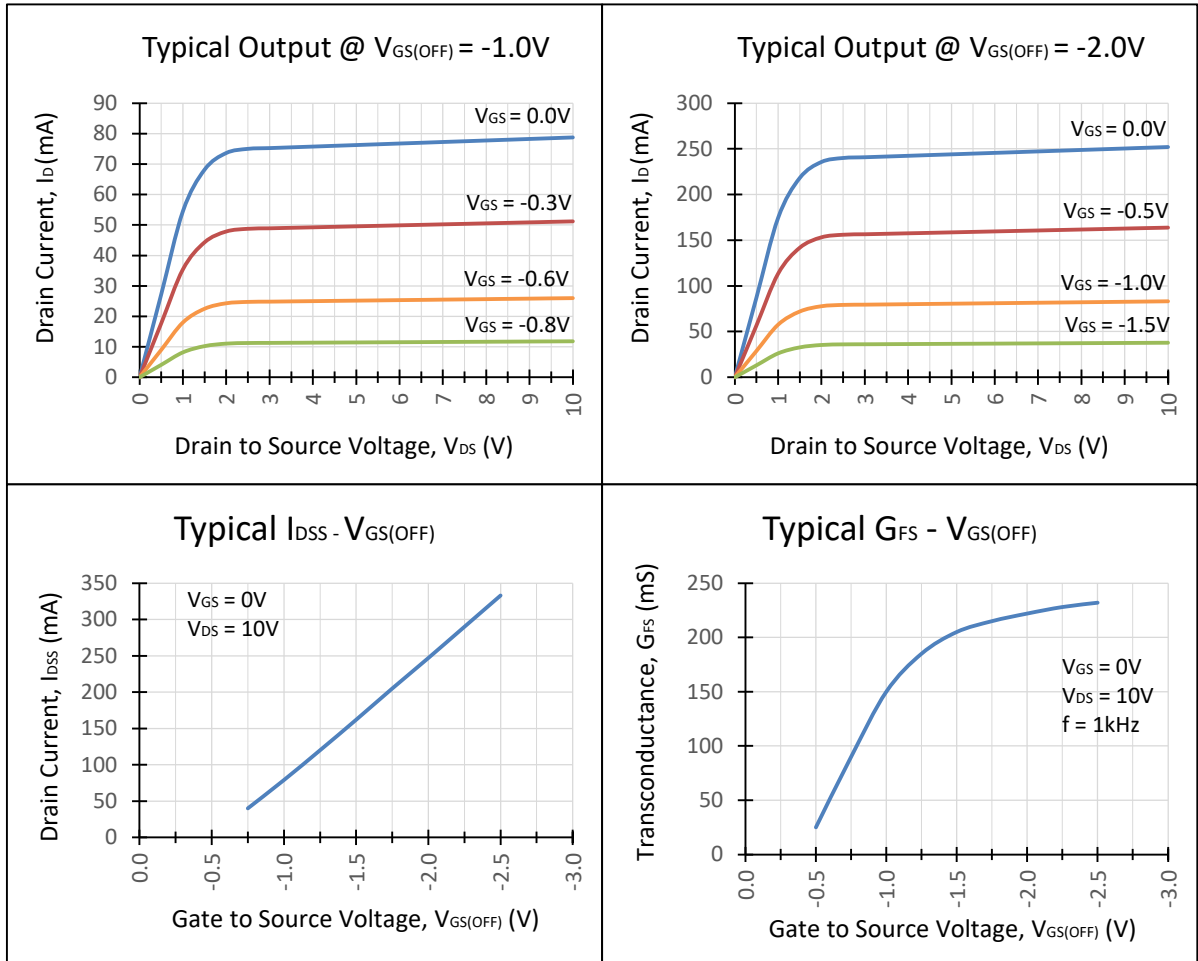
Static Characteristics (@ TA = 25°C, Unless otherwise specified)

Parameters	Conditions	Min	Typ	Max	Unit
BV _{GSS} Gate to Source Breakdown Voltage	I _G = -1μA, V _{DS} = 0V	-20	-30		V
I _{GSS} Gate to Source Reverse Current	V _{GS} = -15V, V _{DS} = 0V		-100	-500	pA
V _{GS(OFF)} Gate to Source Cutoff Voltage	V _{DS} = 10V, I _D = 1nA	-0.3		-3	V
I _{DSS} Drain to Source Saturation Current	V _{DS} = 10V, V _{GS} = 0V	10		500	mA

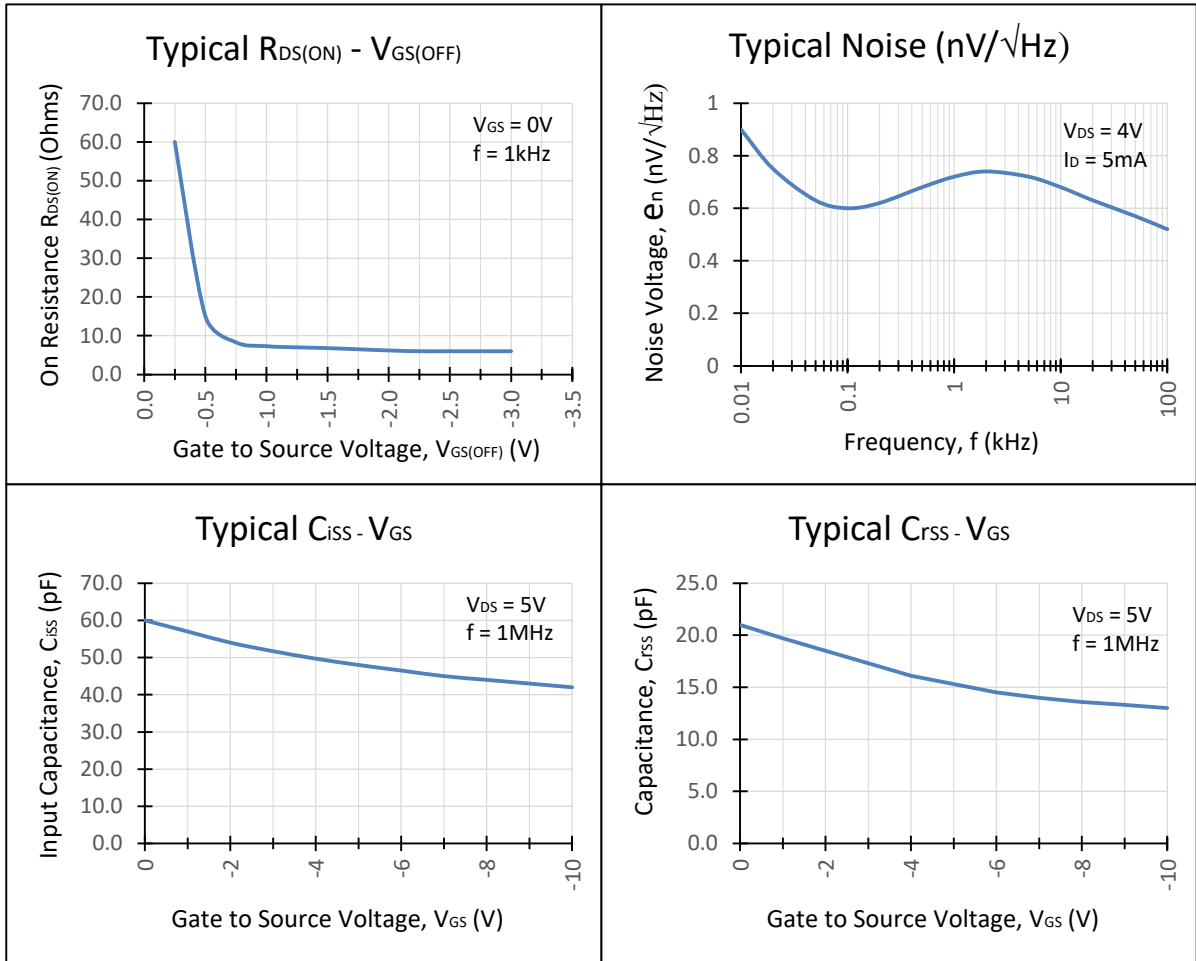
Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

Parameters	Conditions	Min	Typ	Max	Unit
G _{FS} Forward Transconductance	V _{DS} = 15V, V _{GS} = 0V, f = 1kHz		250		mS
C _{iss} Input Capacitance	V _{DS} = 0V, V _{GS} = -10V, f = 1MHz		50		pF
C _{rss} Reverse Transfer Capacitance	V _{DS} = 0V, V _{GS} = -10V, f = 1MHz		18		pF
e _n Noise Voltage	V _{DS} = 4V, I _D = 5mA f = 1kHz		0.7		nV/√Hz

Typical N0903L Characteristics

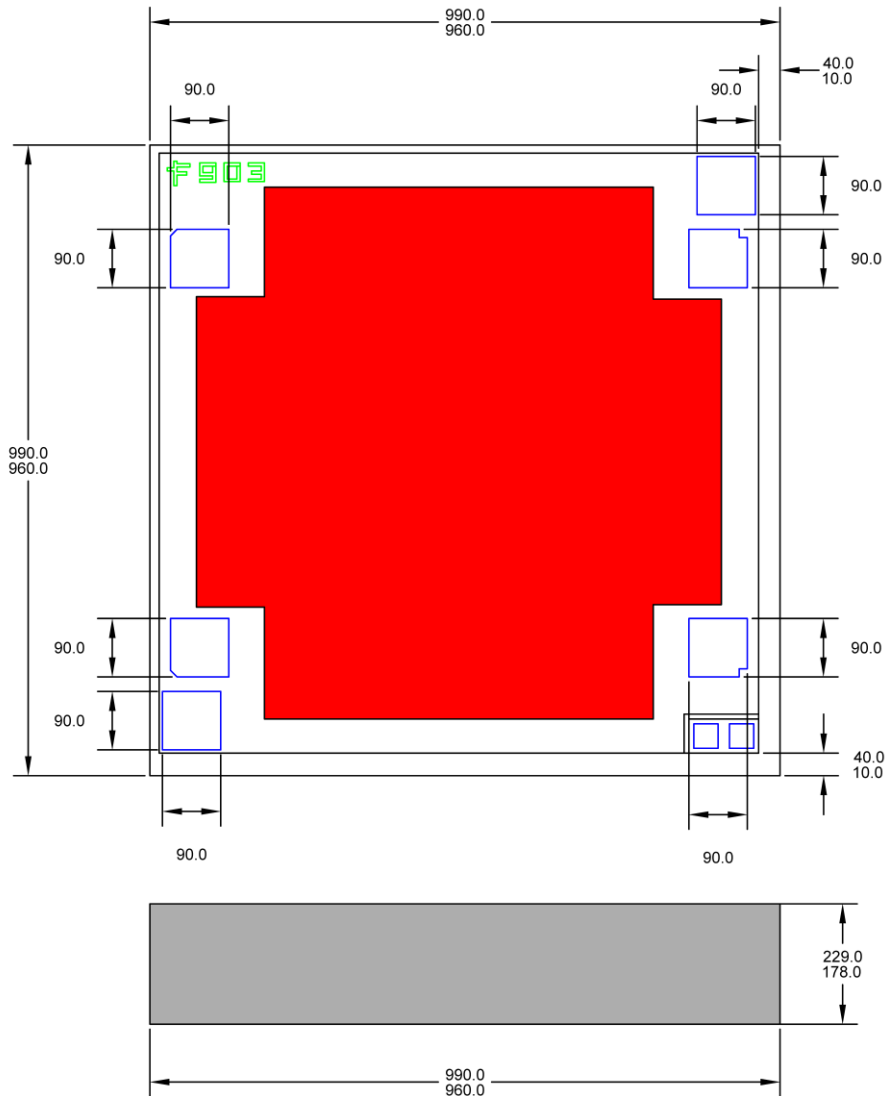


Typical N0903L Characteristics (Continued)



N0903L Die Geometry Mechanical

Raw Die Dimensions



1. All linear dimensions are in micrometers.